



Sheet 1 of 2

Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. <b>30848/40704</b>	Serial No. <b>10/516,384</b>
<b>INFORMATION DISCLOSURE STATEMENT</b>			
Applicant <b>Gogolides et al.</b>		Filing Date <b>May 30, 2003</b>	Group

## **U.S. PATENT DOCUMENTS**

U.S. PATENT DOCUMENTS							
*Examiner Initials		Document Number	Issue Date	Name	Class	Subclass	Filing Date if Appropriate
SJL		2001/0018486A1	08/30/01	Lichtenhan et al.	524	588	
		6,391,471 B1	05/21/02	Hiraoka et al.	428	623	
↓		2003/0022102 A1	01/30/03	Hiraoka et al.	430	270.1	03/07/02

## **FOREIGN PATENT DOCUMENTS**



Sheet 2 of 2

Form PTO-1449 (Modifed)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 30848/40704	Serial No. 10/516,384
<b>INFORMATION DISCLOSURE STATEMENT</b>		Applicant Gogolides et al.	
		Filing Date May 30, 2003	Group

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)			
SJL	"Double Layer Resist System for High Resolution Lithography", Hatzakis et al., Proc. Microcircuit Engnrg. Lausanne, 1981, pp. 386-396		
	"Linear Hybrid Polymer Building Blocks: Methacrylate-Functionalized Polyhedral Oligomeric Silsesquioxane Monomers and Polymers", Lichtenhan et al., Macromolecules 28, 1995, pp. 8435-8437		
	"Extension of 248 nm Optical Lithography: A Thin Film Imaging Approach", Lin et al., SPIE Vol. 3333, 1998, pp. 278-288		
	"Outlook for 157-nm Resist Design", Kunz et al., SPIE Vol. 3678, March 1999, pp. 13-20		
	"Incorporation of Polyhedral Oligosilsesquioxane in Chemically Amplified Resists to Improve Their Reactive Ion Etching Resistance", Wu et al., J. Vac. Sci. Technol. B 19(3), May/June 2001, pp. 851-855		
	"Novel CA Resists with Photoacid Generator in Polymer Chain", Wu et al., SPIE Vol. 4345, 2001, pp. 521-527		
	"Novel Positive-Tone Chemically Amplified Resists with Photoacid Generator in the Polymer Chains", Wu et al., Adv. Mater 13, No. 9, May 2001, pp. 670-672		
	"Silicon-Containing Resists for 157 nm Applications", Sooriyakumaran et al., SPIE Vol. 4345, 2001, pp. 319-326		
	"Recent Advances in Resists for 157 nm Microlithography", Trinque et al., J. Vac. Sci. Technol. B 20(2), March/April 2002, pp. 531-536		
↓	International Search Report in PCT/GB03/00018 dated September 23, 2003		

Examiner	<i>J. F. Lee</i>	Date Considered	<i>9-30-'07</i>
----------	------------------	-----------------	-----------------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.